Zibo Seno Electronic Engineering Co., Ltd.



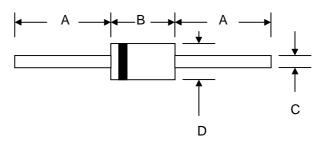
1A1 – 1A7 Contraction of the standard diode

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: R-1, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.181 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version,



R-1						
Dim	Min	Max				
Α	20.0	—				
В	2.90	3.50				
С	0.53	0.64				
D	2.20	2.60				
All Dimensions in mm						

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

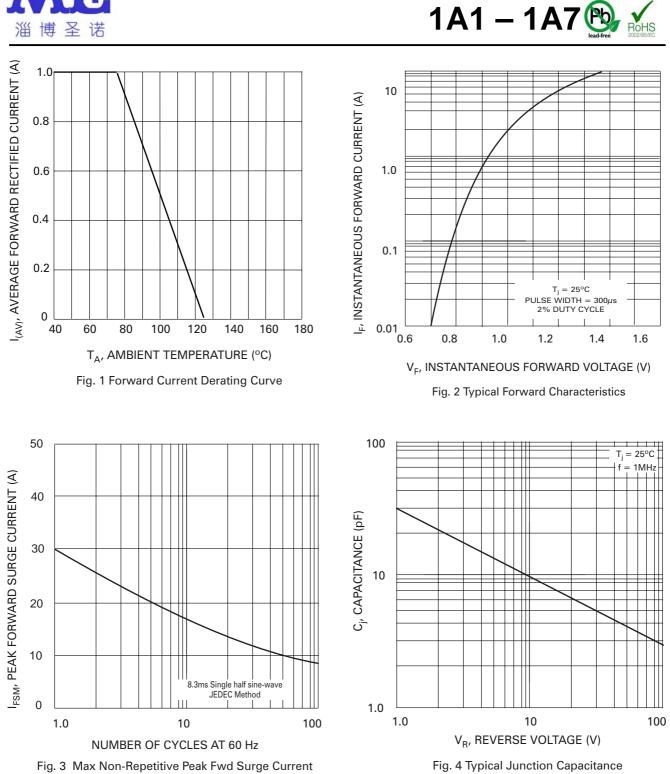
Characteristic	Symbol	1A1	1A2	1A3	1A4	1A5	1A6	1A7	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @ $T_A = 75^{\circ}C$	lo	1.0						А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30						A	
Forward Voltage $@I_F = 1.0A$	Vfm	1.0						V	
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Irm	5.0 50						μA	
Typical Junction Capacitance (Note 2)	Cj	15							pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R ∂ JA	50						°C/W	
Operating Temperature Range	Tj	-65 to +125							°C
Storage Temperature Range	Тѕтс	-65 to +150							°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

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